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California State University of Northridge
Department of Electrical & Computer Engineering

Experiment 12
Design of Common Drain Amplifiers

ECE 340L
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Introduction:

The purpose of this experiment was to design and implement a common source amplifier using the MOSFET 2n7000 and under the following specifications.

$$A_v \geq |V_o/V_i| \geq .95$$

$$Z_i \geq 50 \text{ k}\Omega$$

$$Z_o = 150 \Omega \pm 20\%$$

$$V_o \text{ swing} \geq 2V_{p-p}$$

$$R_L = 5\text{k}\Omega$$

$$V_{cc} \leq 20\text{V}$$

This experiment will verify the theory behind MOSFETs discussed in lecture on Common drain amplifiers such as the gain calculations and input and output impedance.

Equipment:

| Type | Model |
|--------------------|-------------------------------|
| Oscilloscope | Agilent Technologies DSO1002A |
| Digital Multimeter | Tektronix CDM250 |
| Function Generator | Agilent 3322OA |
| Power supply | Hewlett Packard E3630A |

Parts used:

| QTY | Component | Value | Type |
|-----|------------|------------------|---------------------------|
| 1 | Resistor | 10 Ω | Carbon +/- 5% |
| 1 | Resistor | 100 Ω | Carbon +/- 5% |
| 1 | Resistor | 150 Ω | Carbon +/- 5% |
| 1 | Resistor | 1 k Ω | Carbon +/- 5% |
| 1 | Resistor | 100 k Ω | Carbon +/- 5% |
| 1 | Resistor | 150 k Ω | Carbon +/- 5% |
| 1 | Resistor | 5.1 k Ω | Carbon +/- 5% |
| 1 | Resistor | 10 k Ω | Carbon +/- 5% |
| 2 | Capacitor | 10 μF | Polypropylene film +/- 5% |
| 1 | Transistor | 2N7000 | MOSFET |

Software:

Pspice

Microsoft Word

Microsoft Excel

Procedure & Results:

Figure 1 was constructed with the following resistor values

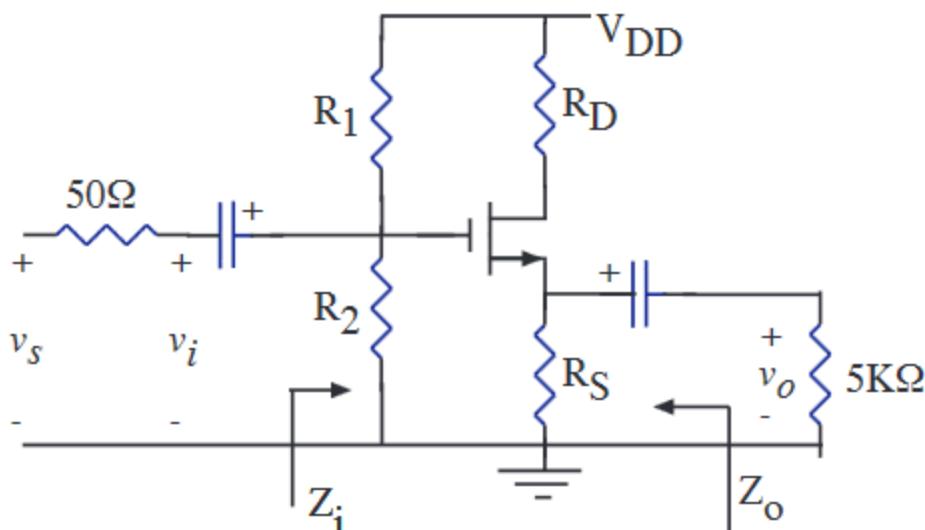
$$R_1 = 150 \text{ k}\Omega$$

$$R_2 = 100 \text{ k}\Omega$$

R_D = short circuit

$$R_S = 10 \text{ k}\Omega$$

Figure 1.



The circuit was then powered by a DC component only and its DC bias values were recorded in the Table 1.

Table 1.

| | V_gs | V_ds | V_d | V_s | V_g | I_d |
|----------|-------|-------|-------|-------|-------|-------|
| calc | 2.19 | 13 | 18 | 5 | 7.2 | 0.5 |
| measured | 2.18 | 13.26 | 18.32 | 5.06 | 7.22 | 0.506 |
| % error | 0.46% | 1.96% | 1.75% | 1.19% | 0.28% | 1.19% |

Q Point.

The Q-point was calculated to be $V_{DS} = 13$ v with an I_D of 0.5 mA.

The measured Q - point was $V_{DS} = 13.26$ v and a current of 0.506 mA.

These values are significantly close to each other and shows that the circuit was operating correctly. The % error was on all our measured values are less than 2% which the theory behind these values.

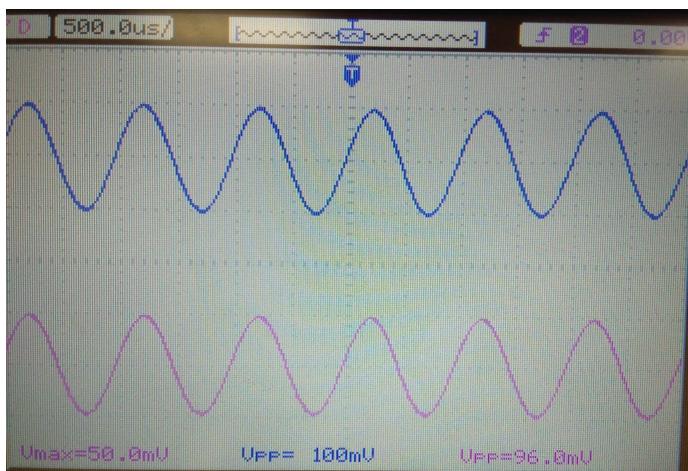
Gain measurements

The 100mV_{P-P} input wave was applied to the gate of the MOSFET. The input and the output across the load were measured and displayed in Oscilloscope 1. The gain was measured to be the following.

$$A_v = \frac{\text{input}}{\text{output}} = \frac{96 \text{ mV}}{100 \text{ mV}} = 0.96$$

These meets the design specification of $A_v \geq |V_o/V_i| \geq .95$

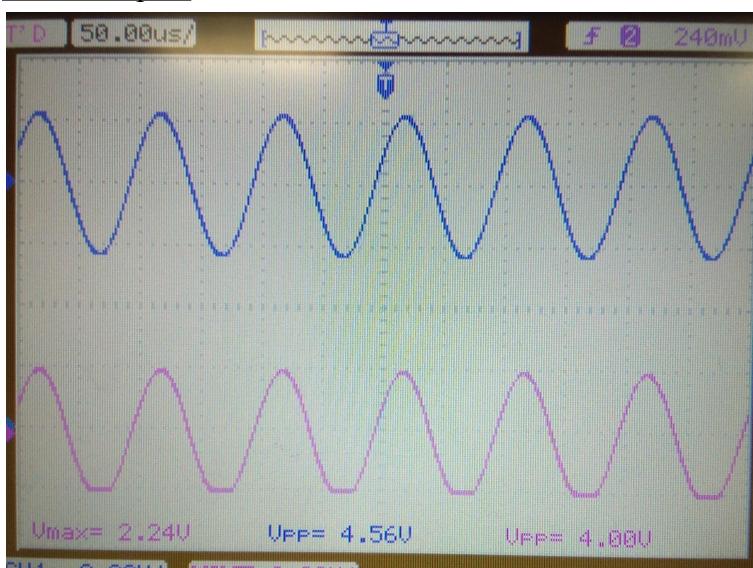
Oscilloscope 1.



Hard clipping

The input signal was increased in amplitude until the Hard Clipping occurred in the output signal. At least, a 2v swing was expected. Oscilloscope 2 shows the results where clipping occurred at 2.24 V_{P-P} and a swing of 2.32 v.

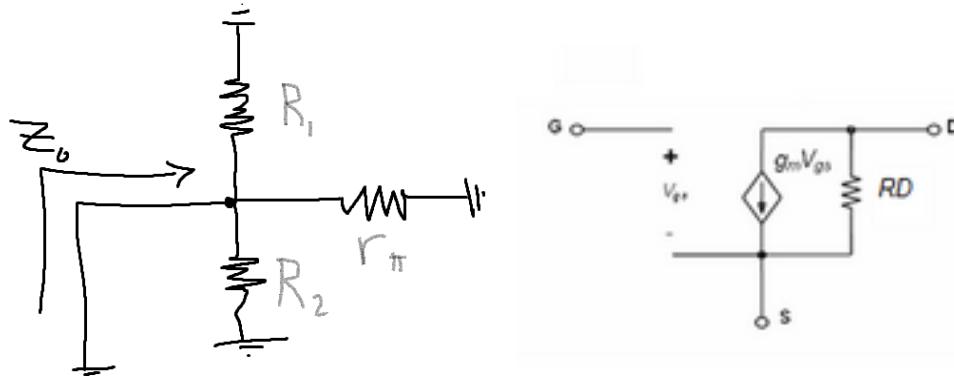
Oscilloscope 2.



Input impedance

Since the input was applied to the Gate of the MOSFET. The input impedance was calculated by finding the terminal resistance of the gate. This was done by using Thevenin's theorem.

Figure 2 Thevenin of input impedance.



$$Z_i = R_1 \parallel R_2 \parallel r_\pi$$

In a MOSFET, r_π is considered to be infinite and is modeled by an open circuit. Given $r_\pi = \infty$, Input impedance is the following.

$$Z_i = R_1 \parallel R_2 = \frac{R_1 * R_2}{R_1 + R_2} = \frac{150 \text{ k}\Omega * 100 \text{ k}\Omega}{150 \text{ k}\Omega + 100 \text{ k}\Omega} = 60 \text{ k}\Omega$$

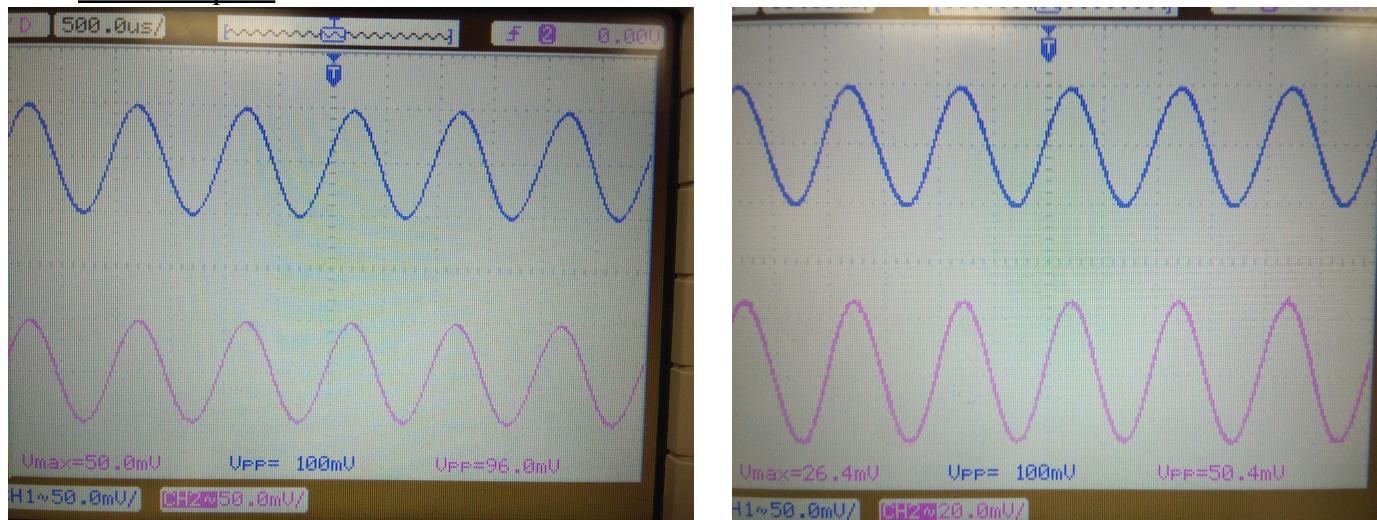
The input impedance of our circuit was measured by adding a value R_s in series at the input of the circuit until the output voltage was decreased by half.

The V_1 was measured to be 96 mV_{P-P}.

V_2 was found to be 48 mV at an R_s value of 62 kΩ.

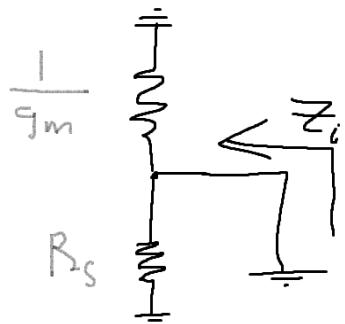
Oscilloscope 3 displays these results.

Oscilloscope 3.



Output impedance

The output was tied to the Source of the MOSFET. The thevenin equivalent is displayed in Figure 3.

Figure 3. Thevenin of output resistance.

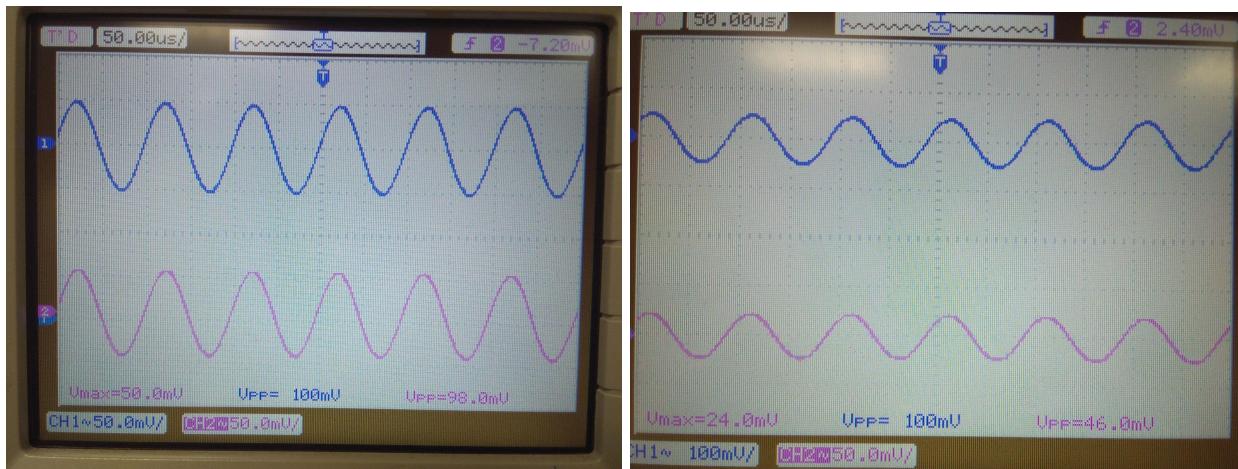
$$Z_i = R_S \parallel (1/g_m)$$

Given that $R_S \gg (1/g_m)$ the following approximation is true.

$$Z_i = (1/g_m)$$

The load was removed and V_1 was recorded to be 98 mV.

A load resistance was added until the output voltage was recorded to be 49 mV.
This value was found at a R_L of 150 Ω .

Oscilloscope 4.

Current and Power gain

The current gain was calculated using ohm's law of the input voltage and the input impedance.

$$I_{in} = V_{in} / Z_i = 100 \text{ mV} / 60k\Omega = 1.612 \mu\text{A}$$

$$I_{out} = V_{out} / Z_o = 96 \text{ mV} / 150 \Omega = 64 \text{ mA}$$

$$A_I = 64 \text{ mA} / 1.62 \mu\text{A} = 39680 \approx \infty$$

$$P_{IN} = V_{in} * I_{in} = 100 \text{ mV} * 1.62 \mu\text{A}$$

$$P_{OUT} = V_{out} * I_{out} = 96 \text{ mV} * 64 \text{ mA}$$

$$A_P = 41333 \approx \infty$$

Power vs Load resistance

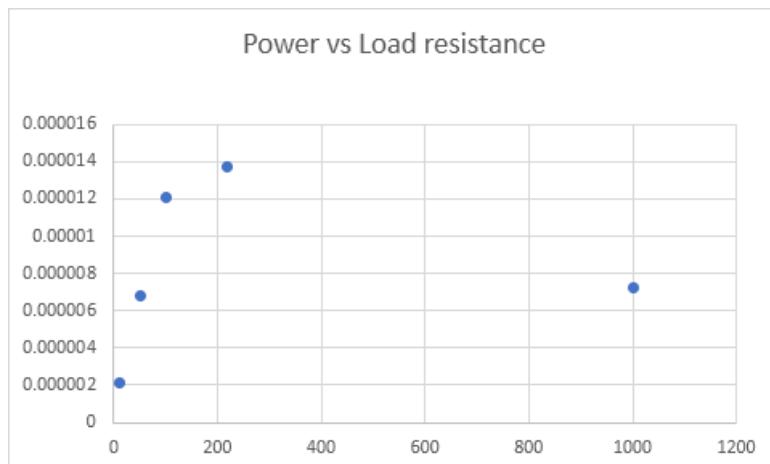
The 5.1 k resistor was removed once again and replaced with values of $R_L = 10, 50, 100, 220, 1000 \Omega$. The output voltage across the loads were recorded in Table 2. The power was calculated by the following.

$$P = V^2 / R.$$

Table 2. Power vs Load

Graph 1.

| V_o(mV) | R_L | P_o |
|---------|------|-------------|
| 4.6 | 10 | 0.000002116 |
| 18.6 | 51 | 6.78353E-06 |
| 34.8 | 100 | 1.21104E-05 |
| 55 | 220 | 0.00001375 |
| 85 | 1000 | 0.000007225 |



Maximum power occurs at 220Ω . If 150Ω was tested it most likely would have been the largest power.

The Maximum power theorem states that when the load is equivalent to the resistance of the circuit the power dissipated across the load is at its peak.